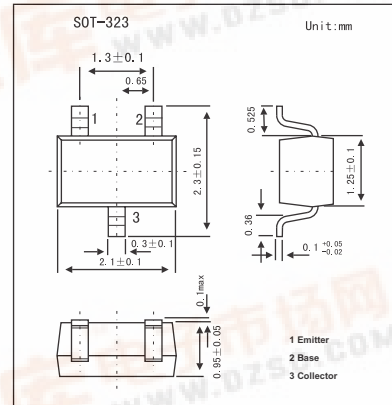


SMD Type Transistors

General Small Signal Amplifier
2SA1980UF

Features

- Low collector saturation voltage.
- Low output capacitance.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-150	mA
Collector dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =-10μA, I _c =0	-5			V
Collector cutoff current	I _{CB0}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =-5V, I _c =0			-0.1	μA
DC current transfer ratio	h _{FE}	V _{CE} =-6V, I _c =-2mA	70		700	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100mA, I _B =-10mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _c =-1mA	80			MHz
Output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		4	7	pF
Noise figure	NF	V _{CE} =-6V, I _c =-0.1mA, f=1KHz, R _g =10KΩ			10	dB

hFE Classification

Marking	C			
	O	Y	G	L
h _{FE}	70~140	120~240	200~400	300~700

